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Attorney Docket No. 0756-1936

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: February 23, 1999

Group: 2812

U.S. PTO
09/25577

02/23/99


U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
AB	4,727,044	2/23/88	Yamazaki	—	—	
AB	4,959,700	9/25/90	Yamazaki	—	—	
AB	5,142,344	5/24/91	Yamazaki	—	—	
AB	4,415,383	11/15/83	Naem et al.	—	—	
AB	4,523,962	6/18/85	Nishimura	—	—	
AB	4,431,459	2/14/84	Teng	—	—	
AB	4,851,363	7/25/89	Troxel et al.	—	—	
AB	4,959,700	9/25/90	Yamazaki	—	—	2/3/88
AB	5,306,651	4/26/94	Masumo et al.	437	40	5/10/91
AB	4,561,906	12/31/85	Calder et al.	437	101	10/24/83
AB	5,091,334	2/25/92	Yamazaki et al.	437	101	6/29/81
AB	5,272,361	12/21/93	Yamazaki	257	66	6/13/90

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
AB	59-121876	7/14/84	Japan	—	—	Abst	
AB	60-245174	12/4/85	Japan	—	—	Abst	
AB	6-59280	3/4/94	Japan	—	—	Abst	
AB	5-206468	8/13/93	Japan	—	—	Abst	
AB	1-187983	7/27/89	Japan	—	—	Abst	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AB		Sameshima et al., Japanese Journal of Applied Physics, "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Vol. 28, No. 10, October, 1989, p. 1789-1793.	
BP		Sera et al., "High Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous Silicon Film", IEEE Transactions, 36 (1989), p. 2868-2872.	
Examiner			Date Considered 2/24/00

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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NS	5,077,235	12/31/91	Kosaka	437	72	1/16/90
NS	5,306,651	4/26/94	Masumo et al.	437	40	5/10/91
NS	4,814,292	3/21/89	Sasaki et al.	437	101	6/19/87
NS	5,298,434	3/29/94	Strater et al.	437	21	2/7/92
NS	5,313,076	5/17/94	Yamazaki et al.	257	66	3/17/92
NS	4,727,044	2/23/88	Yamazaki	437	45	

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
NS	0 023 429	5/82	Japan	437	978		
NS	0 178 447	4/86	Japan	437	173		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

NS	Kiang et al., "Modification of S/C Device Chas. by Lasers", IBM, 1982, p. 171-6.
NS	Sameshima et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Mat. Res Soc. Symp Proc. Vol. 71, 1986, p. 435-440.
NS	Iwamatsu et al., "Silicon on Saaphire MOSFETs Fabricated by Back Surface Laser Anneal Technology", Electronics Letters, Vol. 15, No. 25, p. 827-828, December, 1979.

Examiner

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